

## MOSFET

### 600V CoolMOS™ G7 Power Transistor

The C7 GOLD series (G7) for the first time brings together the benefits of the C7 GOLD CoolMOS™ technology, 4 pin Kelvin Source capability and the improved thermal properties of the DDPAK package to enable a possible SMD solution for high current topologies such as PFC up to 3kW.

#### Features

- C7 Gold gives best in class FOM  $R_{DS(on)} * E_{oss}$  and  $R_{DS(on)} * Q_g$ .
- Suitable for hard and soft switching (PFC and high performance LLC)
- C7 Gold technology enables best in class  $R_{DS(on)}$  in smallest footprint.
- DDPAK package has inbuilt 4<sup>th</sup> pin Kelvin Source configuration and low parasitic source inductance (~3nH).
- DDPAK package is MSL1 compliant, total Pb-free, has easy visual inspection leads and is qualified for industrial applications according to JEDEC 47/20/22.
- DDPAK SMD package combined with lead free die attach process enables improved thermal performance ( $R_{th}$ ).

#### Benefits

- C7 Gold FOM  $R_{DS(on)} * Q_g$  is 15% better than previous C7 600V enabling faster switching leading to higher efficiency.
- Possibility to increase economies of scales by usage in PFC and PWM topologies in the application.
- C7 Gold can reach 50mΩ in DDPAK 115mm<sup>2</sup> footprint, whereas previous BIC C7 600V was 40mΩ in 150mm<sup>2</sup> D<sup>2</sup>PAK footprint.
- Reducing parasitic source inductance by Kelvin Source improves efficiency by faster switching and ease of use due to less ringing.
- DDPAK package is easy to use and has the highest quality standards.
- Improved thermals enable SMD DDPAK package to be used in higher current designs than has been previously possible.

#### Potential applications

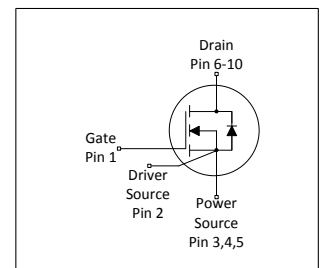
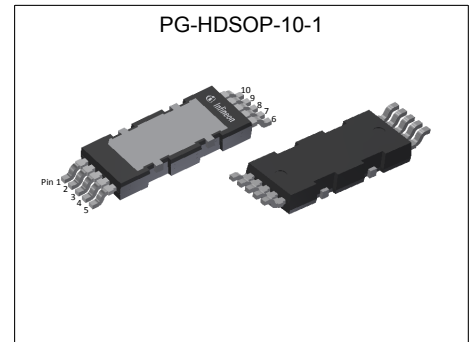
PFC stages and PWM stages (TTF, LLC) for high power/performance SMPS e.g. Computing, Server, Telecom, UPS and Solar.

*Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.*

**Table 1 Key Performance Parameters**

Parameter	Value	Unit
$V_{DS}@T_{j,max}$	650	V
$R_{DS(on),max}$	190	mΩ
$Q_{g,typ}$	18	nC
$I_{D,pulse}$	36	A
$I_{D,continuous} @ T_j < 150^\circ C$	19	A
$E_{oss}@400V$	2.17	μJ
Body diode di/dt	680	A/μs

Type / Ordering Code	Package	Marking	Related Links
IPDD60R190G7	PG-HDSOP-10	60R190G7	see Appendix A



## Table of Contents

Description .....	1
Maximum ratings .....	3
Thermal characteristics .....	4
Electrical characteristics .....	5
Electrical characteristics diagrams .....	7
Test Circuits .....	11
Package Outlines .....	12
Appendix A .....	13
Revision History .....	14
Trademarks .....	14
Disclaimer .....	14

**1 Maximum ratings**  
 at  $T_j=25^\circ\text{C}$ , unless otherwise specified

**Table 2 Maximum ratings**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current <sup>1)</sup>	$I_D$	-	-	13 8	A	$T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$	-	-	36	A	$T_C=25^\circ\text{C}$
Avalanche energy, single pulse	$E_{AS}$	-	-	42	mJ	$I_D=2.8\text{A}$ ; $V_{DD}=50\text{V}$ ; see table 10
Avalanche energy, repetitive	$E_{AR}$	-	-	0.21	mJ	$I_D=2.8\text{A}$ ; $V_{DD}=50\text{V}$ ; see table 10
Avalanche current, single pulse	$I_{AS}$	-	-	2.8	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	120	V/ns	$V_{DS}=0\dots400\text{V}$
Gate source voltage (static)	$V_{GS}$	-20	-	20	V	static;
Gate source voltage (dynamic)	$V_{GS}$	-30	-	30	V	AC ( $f>1\text{ Hz}$ )
Power dissipation	$P_{tot}$	-	-	76	W	$T_C=25^\circ\text{C}$
Storage temperature	$T_{stg}$	-55	-	150	$^\circ\text{C}$	-
Operating junction temperature	$T_j$	-55	-	150	$^\circ\text{C}$	-
Mounting torque	-	-	-	n.a.	Ncm	-
Continuous diode forward current	$I_S$	-	-	13	A	$T_C=25^\circ\text{C}$
Diode pulse current <sup>2)</sup>	$I_{S,pulse}$	-	-	36	A	$T_C=25^\circ\text{C}$
Reverse diode dv/dt <sup>3)</sup>	dv/dt	-	-	25	V/ns	$V_{DS}=0\dots400\text{V}$ , $I_{SD}\leq 4.3\text{A}$ , $T_j=25^\circ\text{C}$ see table 8
Maximum diode commutation speed	di/dt	-	-	680	A/ $\mu\text{s}$	$V_{DS}=0\dots400\text{V}$ , $I_{SD}\leq 4.3\text{A}$ , $T_j=25^\circ\text{C}$ see table 8
Insulation withstand voltage	$V_{ISO}$	-	-	n.a.	V	$V_{rms}$ , $T_C=25^\circ\text{C}$ , $t=1\text{min}$

<sup>1)</sup> Limited by  $T_{j,max}$

<sup>2)</sup> Pulse width  $t_p$  limited by  $T_{j,max}$

<sup>3)</sup> Identical low side and high side switch

## 2 Thermal characteristics

**Table 3 Thermal characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{thJC}$	-	-	1.65	°C/W	-
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	62	°C/W	device on PCB, minimal footprint
Thermal resistance, junction - ambient for SMD version	$R_{thJA}$	-	35	45	°C/W	Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm <sup>2</sup> (one layer, 70µm thickness) copper area for drain connection and cooling. PCB is vertical without air stream cooling.
Reflow soldering temperature	$T_{sold}$	-	-	260	°C	reflow MSL1

### 3 Electrical characteristics

at  $T_j=25^\circ\text{C}$ , unless otherwise specified

**Table 4 Static characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	600	-	-	V	$V_{GS}=0\text{V}$ , $I_D=1\text{mA}$
Gate threshold voltage	$V_{(GS)th}$	3	3.5	4	V	$V_{DS}=V_{GS}$ , $I_D=0.21\text{mA}$
Zero gate voltage drain current	$I_{DSS}$	-	-	1	$\mu\text{A}$	$V_{DS}=600\text{V}$ , $V_{GS}=0\text{V}$ , $T_j=25^\circ\text{C}$ $V_{DS}=600\text{V}$ , $V_{GS}=0\text{V}$ , $T_j=150^\circ\text{C}$
Gate-source leakage current	$I_{GSS}$	-	-	100	nA	$V_{GS}=20\text{V}$ , $V_{DS}=0\text{V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.164 0.409	0.190	$\Omega$	$V_{GS}=10\text{V}$ , $I_D=4.2\text{A}$ , $T_j=25^\circ\text{C}$ $V_{GS}=10\text{V}$ , $I_D=4.2\text{A}$ , $T_j=150^\circ\text{C}$
Gate resistance	$R_G$	-	0.9	-	$\Omega$	$f=1\text{MHz}$ , open drain

**Table 5 Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	$C_{iss}$	-	718	-	pF	$V_{GS}=0\text{V}$ , $V_{DS}=400\text{V}$ , $f=250\text{kHz}$
Output capacitance	$C_{oss}$	-	15	-	pF	$V_{GS}=0\text{V}$ , $V_{DS}=400\text{V}$ , $f=250\text{kHz}$
Effective output capacitance, energy related <sup>1)</sup>	$C_{o(er)}$	-	27	-	pF	$V_{GS}=0\text{V}$ , $V_{DS}=0\dots400\text{V}$
Effective output capacitance, time related <sup>2)</sup>	$C_{o(tr)}$	-	277	-	pF	$I_D=\text{constant}$ , $V_{GS}=0\text{V}$ , $V_{DS}=0\dots400\text{V}$
Turn-on delay time	$t_{d(on)}$	-	16	-	ns	$V_{DD}=400\text{V}$ , $V_{GS}=13\text{V}$ , $I_D=4.2\text{A}$ , $R_G=10\Omega$ ; see table 9
Rise time	$t_r$	-	5	-	ns	$V_{DD}=400\text{V}$ , $V_{GS}=13\text{V}$ , $I_D=4.2\text{A}$ , $R_G=10\Omega$ ; see table 9
Turn-off delay time	$t_{d(off)}$	-	52	-	ns	$V_{DD}=400\text{V}$ , $V_{GS}=13\text{V}$ , $I_D=4.2\text{A}$ , $R_G=10\Omega$ ; see table 9
Fall time	$t_f$	-	6.5	-	ns	$V_{DD}=400\text{V}$ , $V_{GS}=13\text{V}$ , $I_D=4.2\text{A}$ , $R_G=10\Omega$ ; see table 9

**Table 6 Gate charge characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	$Q_{GS}$	-	4	-	nC	$V_{DD}=400\text{V}$ , $I_D=4.2\text{A}$ , $V_{GS}=0$ to $10\text{V}$
Gate to drain charge	$Q_{gd}$	-	7	-	nC	$V_{DD}=400\text{V}$ , $I_D=4.2\text{A}$ , $V_{GS}=0$ to $10\text{V}$
Gate charge total	$Q_g$	-	18	-	nC	$V_{DD}=400\text{V}$ , $I_D=4.2\text{A}$ , $V_{GS}=0$ to $10\text{V}$
Gate plateau voltage	$V_{plateau}$	-	5.0	-	V	$V_{DD}=400\text{V}$ , $I_D=4.2\text{A}$ , $V_{GS}=0$ to $10\text{V}$

<sup>1)</sup>  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 400V

<sup>2)</sup>  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 400V

**Table 7 Reverse diode characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	$V_{SD}$	-	0.8	-	V	$V_{GS}=0V, I_F=4.2A, T_j=25^\circ C$
Reverse recovery time	$t_{rr}$	-	235	-	ns	$V_R=400V, I_F=4.2A, di_F/dt=100A/\mu s$ ; see table 8
Reverse recovery charge	$Q_{rr}$	-	2	-	$\mu C$	$V_R=400V, I_F=4.2A, di_F/dt=100A/\mu s$ ; see table 8
Peak reverse recovery current	$I_{rrm}$	-	18	-	A	$V_R=400V, I_F=4.2A, di_F/dt=100A/\mu s$ ; see table 8

### 4 Electrical characteristics diagrams

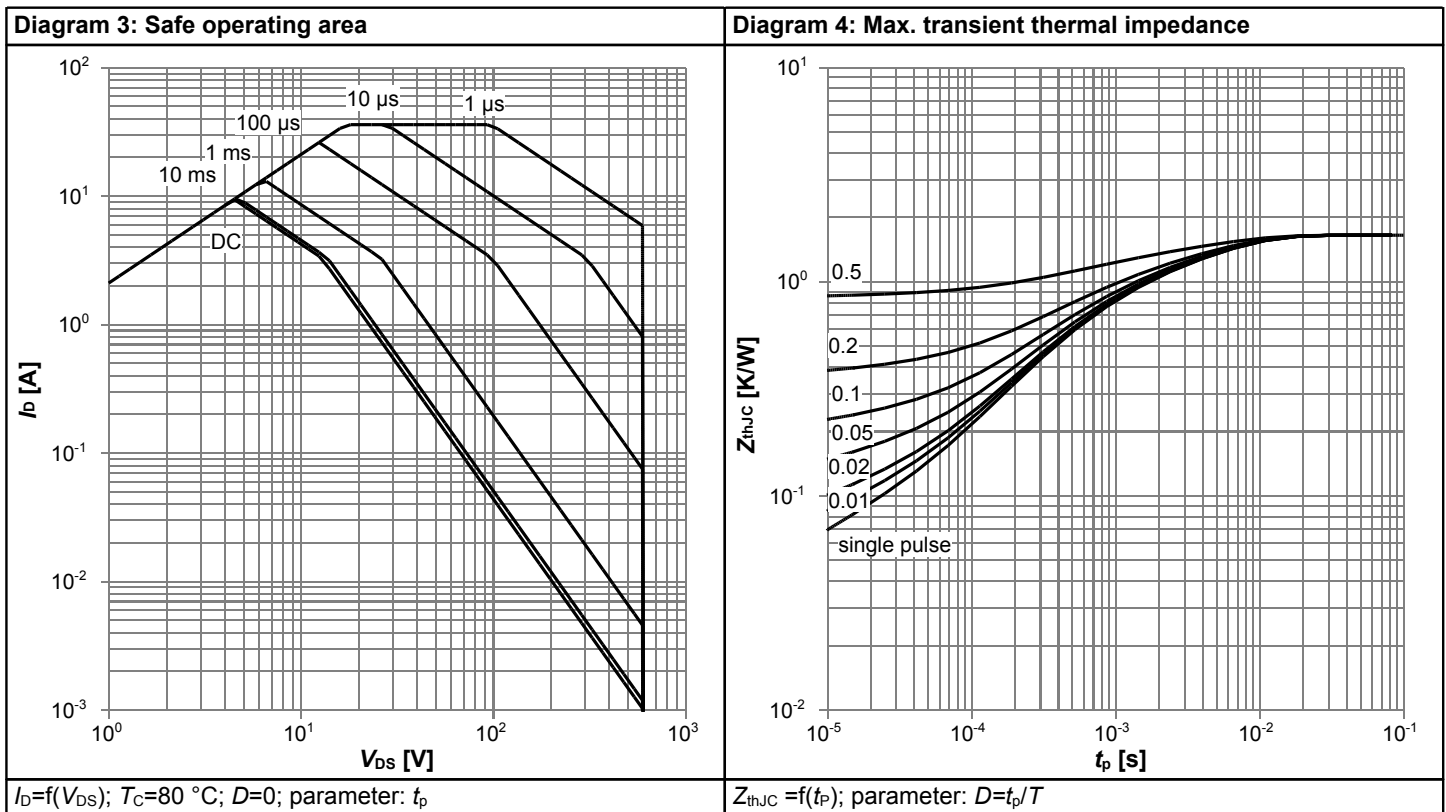
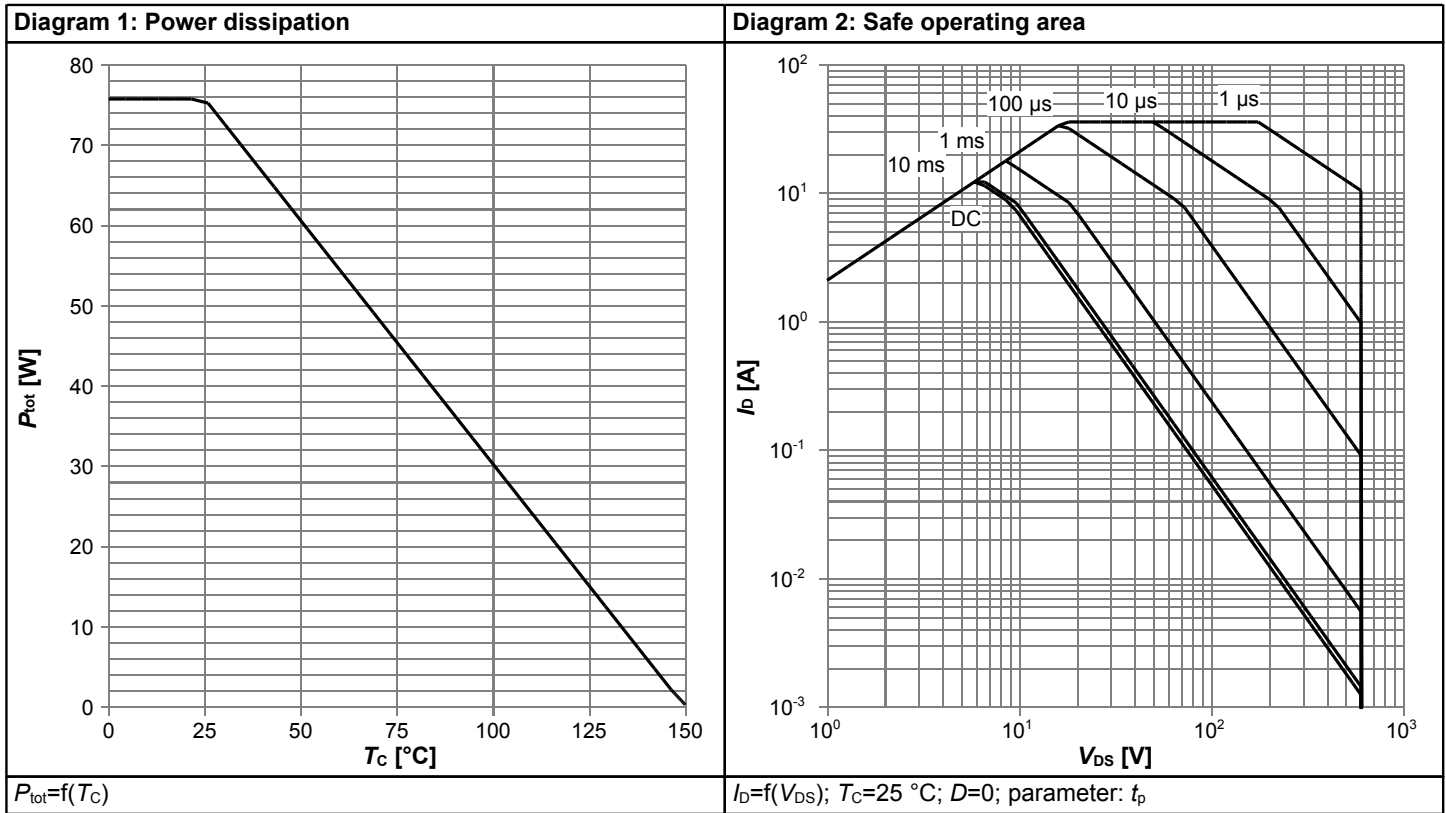
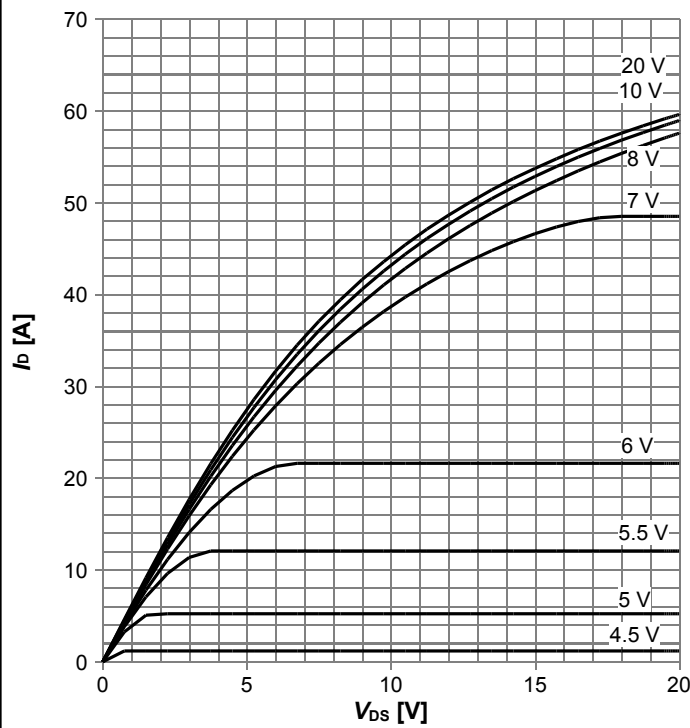
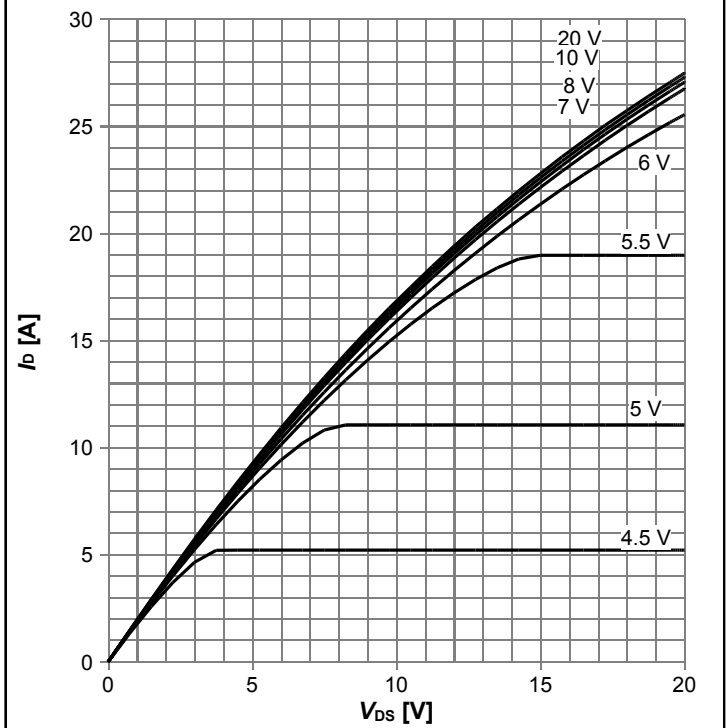


Diagram 5: Typ. output characteristics



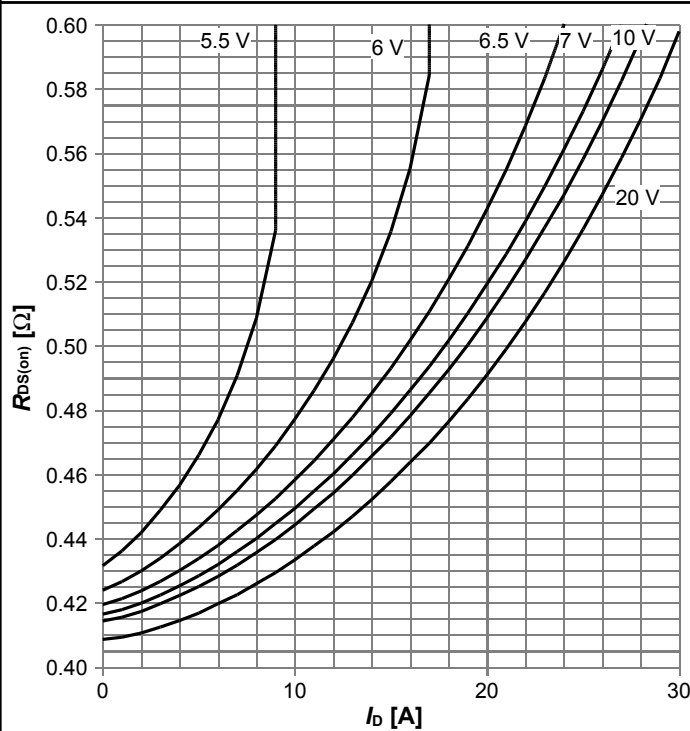
$I_D=f(V_{DS})$ ;  $T_j=25\text{ }^\circ\text{C}$ ; parameter:  $V_{GS}$

Diagram 6: Typ. output characteristics



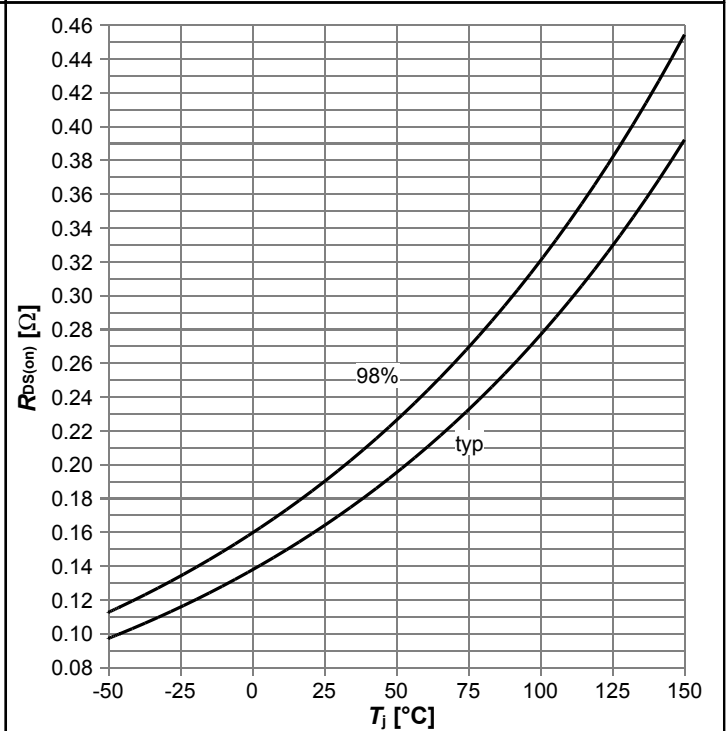
$I_D=f(V_{DS})$ ;  $T_j=125\text{ }^\circ\text{C}$ ; parameter:  $V_{GS}$

Diagram 7: Typ. drain-source on-state resistance



$R_{DS(on)}=f(I_D)$ ;  $T_j=125\text{ }^\circ\text{C}$ ; parameter:  $V_{GS}$

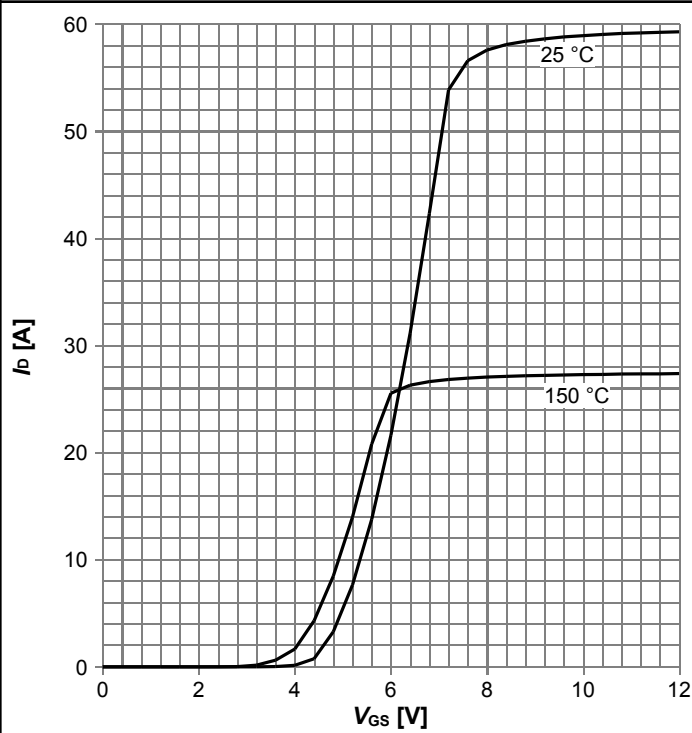
Diagram 8: Drain-source on-state resistance



$R_{DS(on)}=f(T_j)$ ;  $I_D=4.2\text{ A}$ ;  $V_{GS}=10\text{ V}$

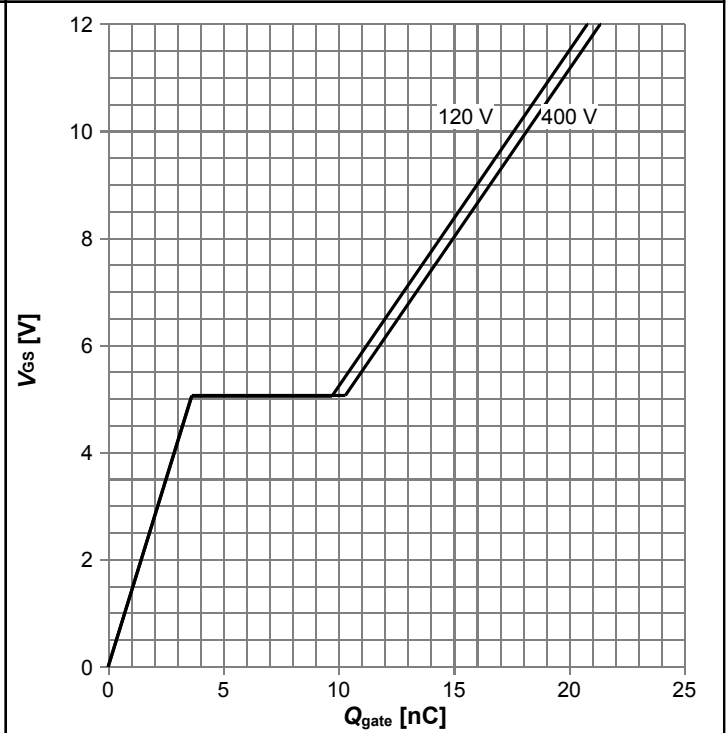


Diagram 9: Typ. transfer characteristics



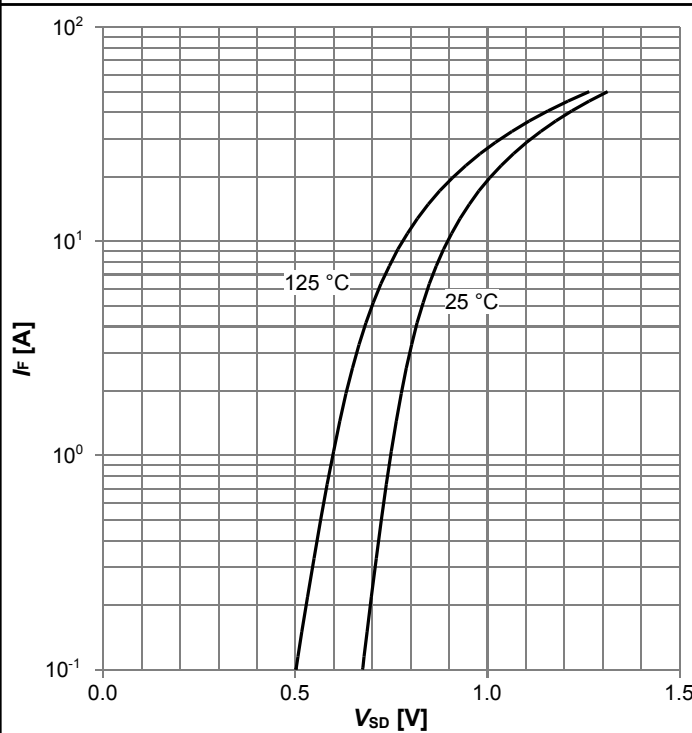
$I_D = f(V_{GS}); V_{DS} = 20V; \text{parameter: } T_j$

Diagram 10: Typ. gate charge



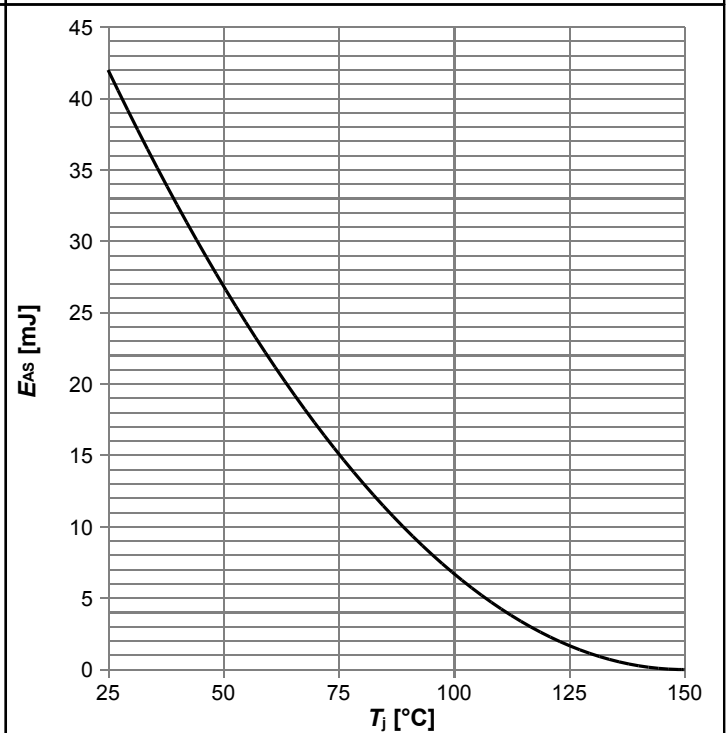
$V_{GS} = f(Q_{gate}); I_D = 4.2 \text{ A pulsed}; \text{parameter: } V_{DD}$

Diagram 11: Forward characteristics of reverse diode



$I_F = f(V_{SD}); \text{parameter: } T_j$

Diagram 12: Avalanche energy

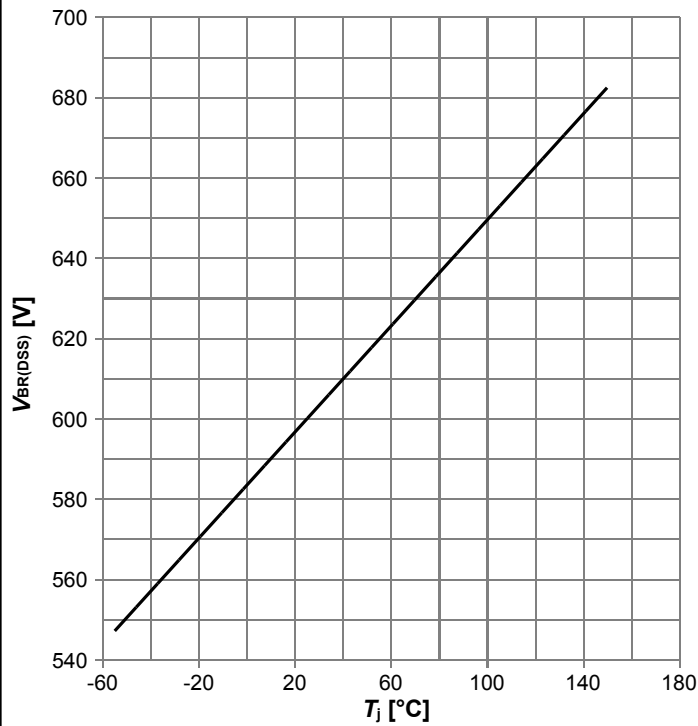


$E_{AS} = f(T_j); I_D = 2.8 \text{ A}; V_{DD} = 50 \text{ V}$

# 600V CoolMOS™ G7 Power Transistor

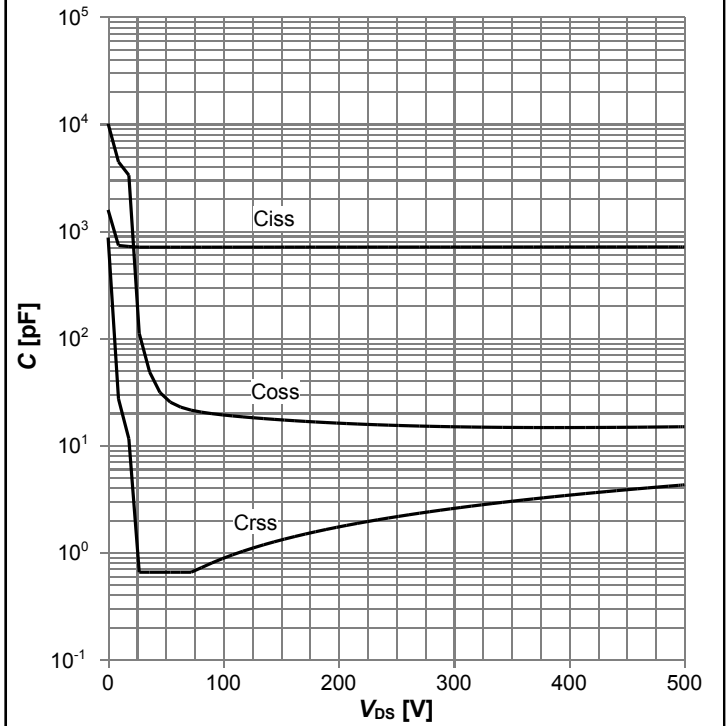
## IPDD60R190G7

**Diagram 13: Drain-source breakdown voltage**



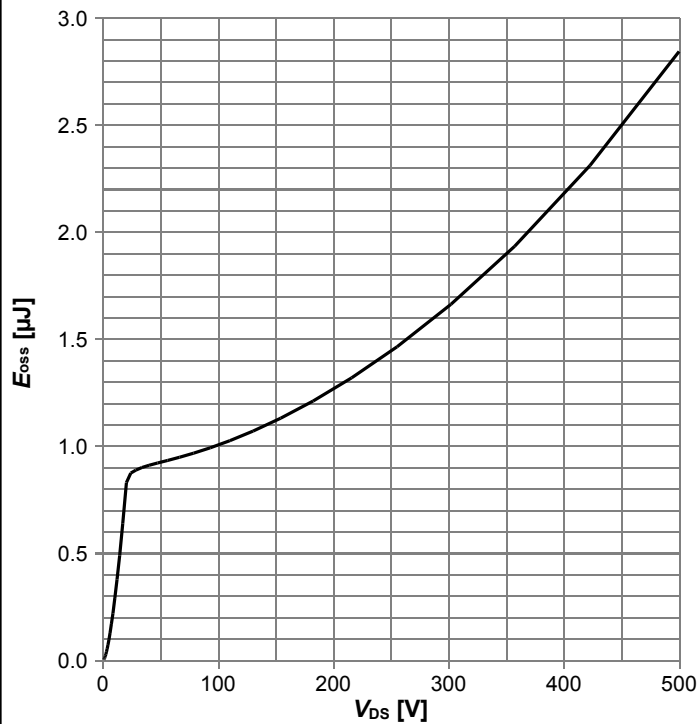
$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

**Diagram 14: Typ. capacitances**



$C=f(V_{DS}); V_{GS}=0 \text{ V}; f=250 \text{ kHz}$

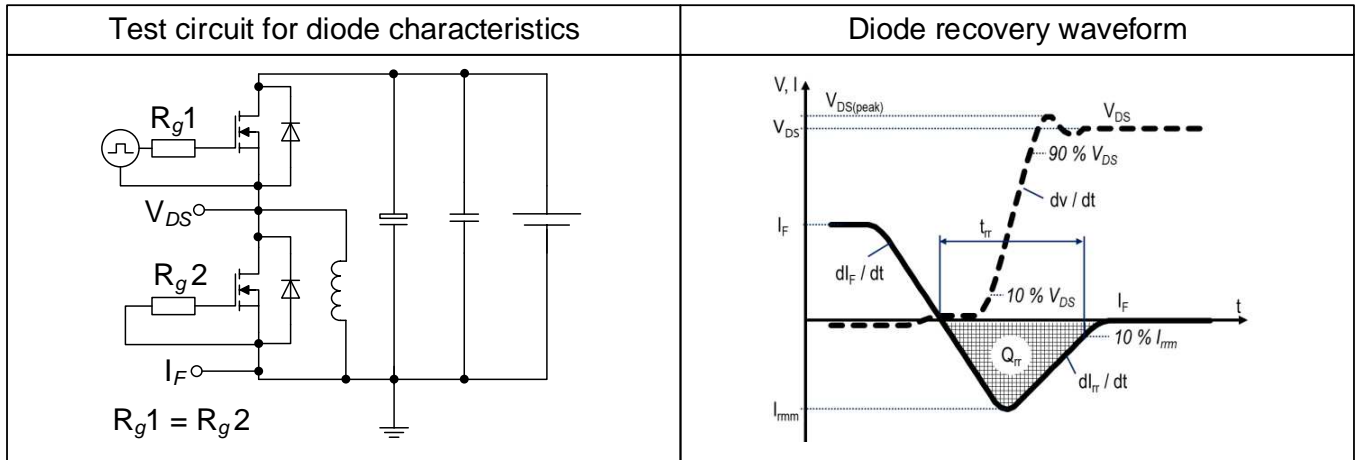
**Diagram 15: Typ. Coss stored energy**



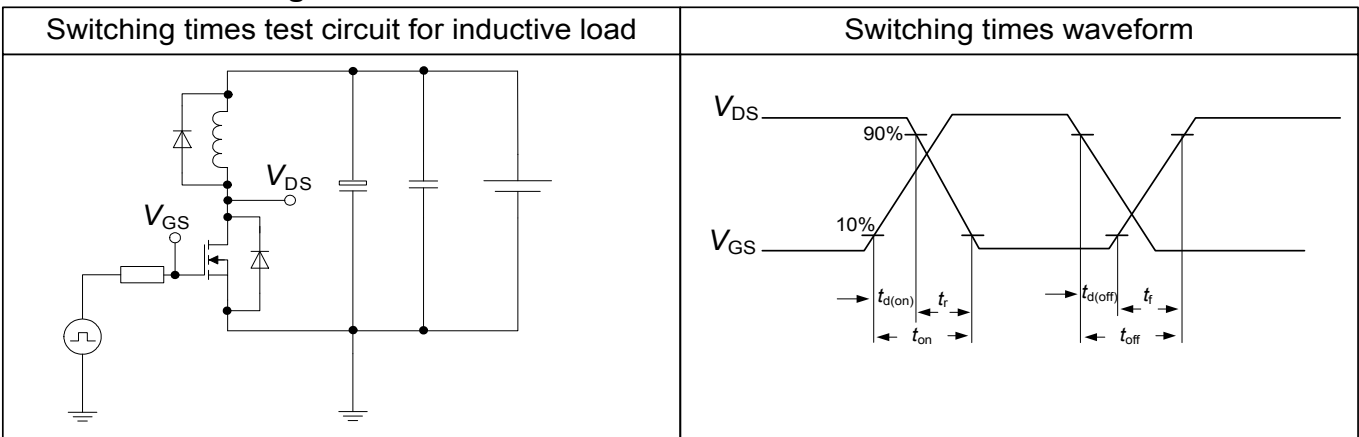
$E_{oss}=f(V_{DS})$

## 5 Test Circuits

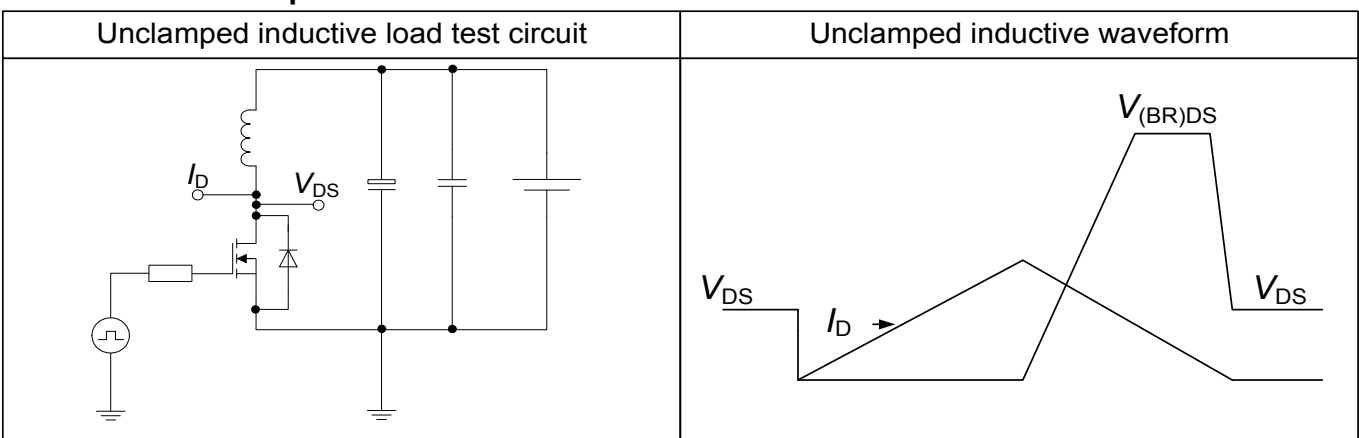
**Table 8 Diode characteristics**



**Table 9 Switching times**



**Table 10 Unclamped inductive load**



6 Package Outlines

PG-HDSOP-10-1

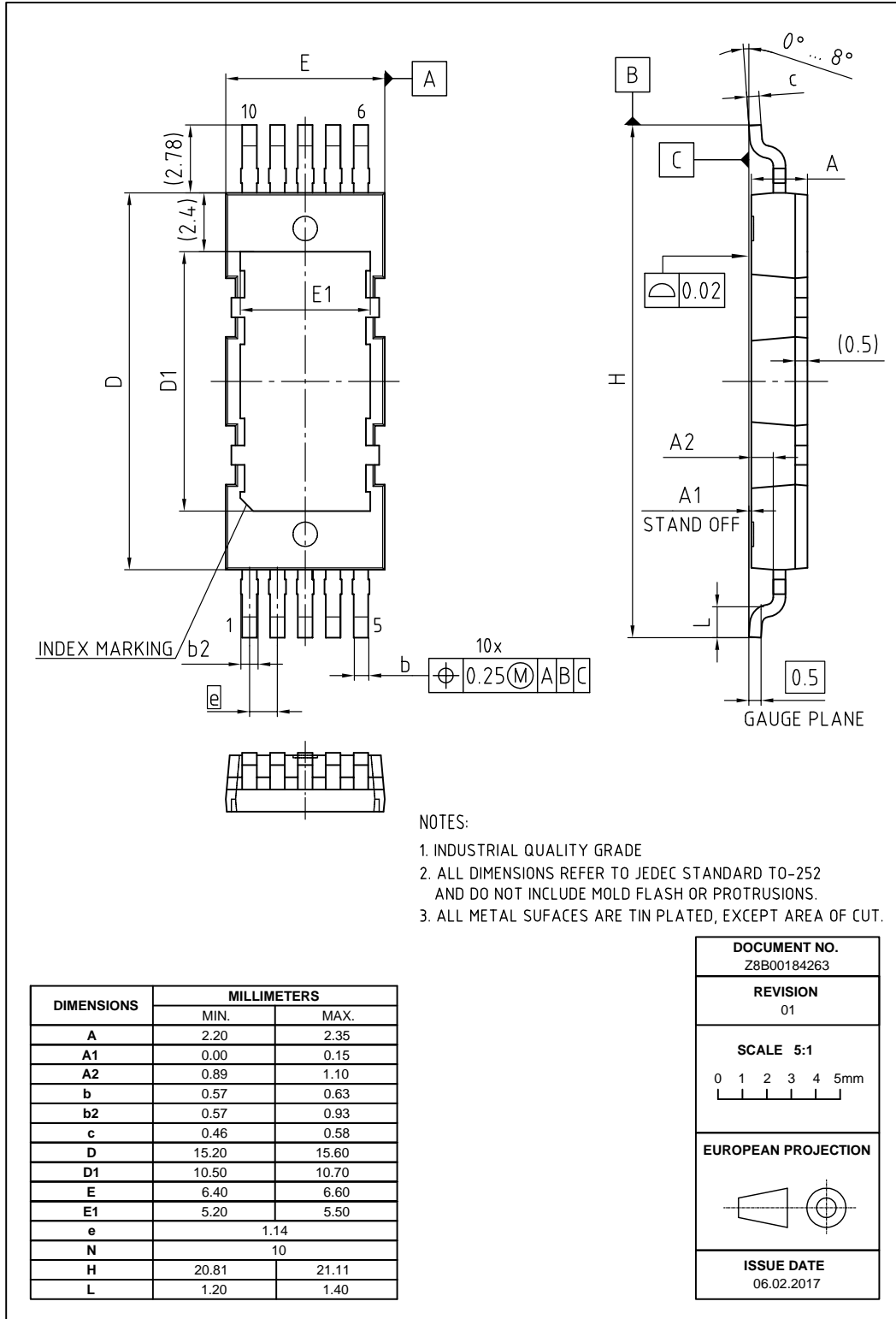


Figure 1 Outline PG-HDSOP-10, dimensions in mm/inches

## 7 Appendix A

Table 11 Related Links

- IFX CoolMOS™ G7 Webpage: [www.infineon.com](http://www.infineon.com)
- IFX CoolMOS™ G7 application note: [www.infineon.com](http://www.infineon.com)
- IFX CoolMOS™ G7 simulation model: [www.infineon.com](http://www.infineon.com)
- IFX Design tools: [www.infineon.com](http://www.infineon.com)

## Revision History

IPDD60R190G7

Revision: 2018-01-05, Rev. 2.0

### Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2018-01-05	Release of final version

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